

YON-0205

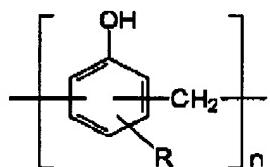
IN THE CLAIMS

1. - 10. (Cancelled)

11. (Currently Amended) A method for applying a photoresist composition to an MMN head coater, wherein the photoresist composition comprises:

- (a) 5 wt% to 30 wt% of a polymer resin represented by the following Chemical Formula 1;
- (b) 2 wt% to 10 wt% of a diazide photoactive compound;
- (c) 50 wt% to 90 wt% of an organic solvent; and
- (d) 500 to 4000 ppm of a Si based surfactant:

Chemical Formula 1



wherein R is C₁ to C₄ alkyl, and n is an integer of 15 to 10,000, and wherein the Si-based surfactant is a polyoxyalkylene dimethylpolysiloxane copolymer compound.

12. (withdrawn) The method of Claim 11,
wherein the polymer resin is a novolak resin having a molecular weight ranging from about 2000 to 12,000.

13. (withdrawn) The method of Claim 11,
wherein the organic solvent is one or more substances selected from the group consisting of propyleneglycol methyl ether acetate (PGMEA), ethyl lactate (EL), 2-methoxyethylacetate (MMP), n-butyl acetate (nBA), propyleneglycol monomethyl ether (PGME), and ethyl-3-ethoxypropionate (EEP).

14. (withdrawn) The method of Claim 11,
wherein the organic solvent is a mixture of 50 wt% to 90 wt% of propyleneglycol methyl ether acetate (PGMEA) and 10 wt% to 50 wt% of ethyl-3-ethoxypropionate (EEP).

YOM-0205

15. (cancelled)

16. (withdrawn) The method of Claim 11,
wherein the composition further comprises one or more nitrogen-containing crosslinking
agents selected from the group consisting of a condensation product of urea and formaldehyde, a
condensation product of melamine and formaldehyde, a methylole urea alkyl aldehyde condensate,
a methylole urea alkylether, and a methylole melamine alkylether.

17. (New) The method of Claim 11, wherein the photoresist composition is
applied by a pattern formation method, comprising:

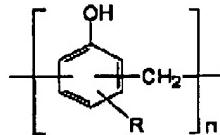
(a) coating the photoresist composition on a substrate and drying it to prepare a
photoresist film;

(b) placing a patterned mask on the substrate and exposing the photoresist film to
light; and

(c) developing the exposed photoresist film to obtain a photoresist pattern, and
wherein the photoresist composition comprises:

5 wt% to 30 wt% of a polymer resin represented by the following Chemical Formula 1
which is a novolak resin having a molecular weight ranging from about 2000 to 12,000; 2 wt% to
10 wt% of a diazide photoactive compound; 50 wt% to 90 wt% of an organic solvent of one or
more substances selected from the group consisting of propyleneglycol methyl ether acetate
(PGMEA), ethyl lactate (EL), 2-methoxyethylacetate (MMP), n-butyl acetate (nBA),
propyleneglycol monomethyl ether (PGME), and ethyl-3-ethoxypropionate (EEP); and 500 to
4000 ppm of a polyoxyalkylene dimethylpolysiloxane copolymer compound as a Si-based
surfactant:

Chemical Formula 1



where R is a C₁ to C₄ alkyl, and n is an integer of 15 to 10,000,

wherein the organic solvent is a mixture of 50 wt% to 90 wt% of propyleneglycol
methyl ether acetate (PGMEA) and 10 wt% to 50 wt% of ethyl-3-
ethoxypropionate(EEP).

YOM-0205

18. (New) The method of Claim 11, wherein the photoresist composition further comprises one or more nitrogen-containing crosslinking agents selected from the group consisting of a condensation product of urea and formaldehyde, a condensation product of melamine and formaldehyde, a methylol urea alkyl aldehyde condensate, a methylol urea alkylether, and a methylol melamine alkylether.

19. (New) The method of Claim 11, wherein the photoresist composition is coated by the spray dispense method or the spin coating method.

20. (New) The method of Claim 11, which is applied to liquid crystal display circuits using a large-scale substrate glass.